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(54) Title: MODULATING A LIGHT BEAM
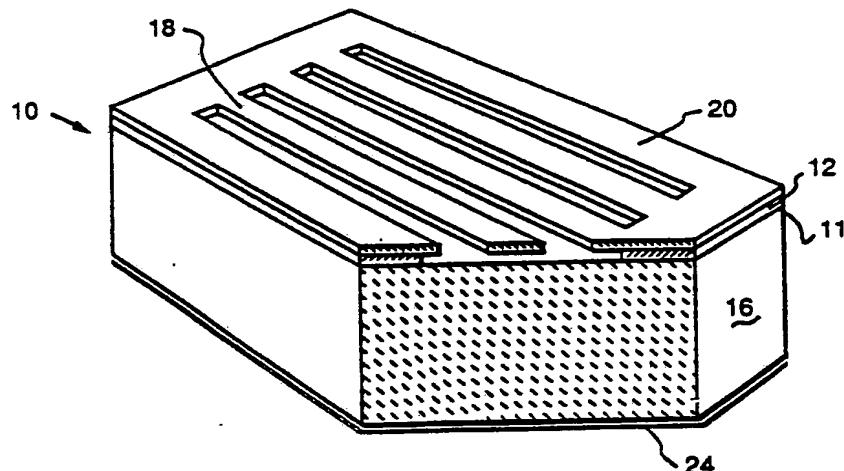
(57) Abstract

A modulator (10) for modulating incident rays of light, the modulator having several equally spaced beam elements (18), each having a light reflective planar surface. The beam elements are arranged and supported (12) parallel to each other, with their reflective surfaces parallel. During operation, the elements remain parallel, but the modulator moves the beams so that the perpendicular spacing of their reflective surfaces changes between two configurations. In both configurations, the spacing equals m/4 times the wavelength of incident light. In the first configuration, m equals an even whole number or zero, and the modulator acts to reflect the incident rays of light as a plane mirror. In the second configuration, m equals an odd number and the modulator diffracts the incident rays as they are reflected.

1   **Specification**
2   **MODULATING A LIGHT BEAM**
3
4   **BACKGROUND OF THE INVENTION**
5
6   **Field of the Invention**
7   This invention relates to a method and apparatus for
8   modulating a light beam and more particularly to the use
9   of a reflective, deformable diffraction grating for
10   performing such modulation.
11
12   **Brief Description of the Prior Art**
13   Devices which modulate a light beam, e.g. by altering
14   the amplitude, frequency or phase of the light, find a
15   number of applications. An example of such a device is a
16   spatial light modulator (SLM) which is an electronically
17   or optically controlled device which consists of one or
18   two-dimensional reconfigurable patterns of pixel elements,
19   each of which can individually modulate the amplitude,
20   phase or polarization of an optical wavefront.
21   These devices have been extensively developed,
22   particularly for applications in the areas of optical
23   processing and computing. They can perform a variety of
24   functions such as: analog multiplication and addition,
25   signal conversion (electrical-to-optical, incoherent-to-
26   coherent, amplification, etc.), nonlinear operations and
27   short term storage. Utilizing these functions, SLMs have
28   seen many different applications from display technology
29   to optical signal processing. For example, SLMs have been
30   used as optical correlators (e.g., pattern recognition
31   devices, programmable holograms), optical matrix
32   processors (e.g., matrix multipliers, optical cross-bar
33   switches with broadcast capabilities, optical neural
34   networks, radar beam forming), digital optical
35   architectures (e.g., highly parallel optical computers)
36   and displays.
37   The requirements for SLM technology depend strongly
38   on the application in mind: for example, a display
39   requires low bandwidth but a high dynamic range while

optical computers benefit from high response times but don't require such high dynamic ranges. Generally, systems designers require SLMs with characteristics such as: high resolution, high speed (kHz frame rates), good gray scale high contrast ratio or modulation depth, optical flatness, VLSI compatible, easy handling capability and low cost. To date, no one SLM design can satisfy all the above requirements. As a result, different types of SLMs have been developed for different applications, often resulting in trade-offs.

Texas Instrument, for instance, has developed a "Deformable Mirror Device (DMD)" that utilizes an electromechanical means of deflecting an optical beam. The mechanical motions needed for the operation of the DMD are relatively large and, as a result, the bandwidths are limited to tens of kilohertz. This device, however, gives good contrast ratios and high-resolution and is, furthermore, compatible with CMOS, and other low power technologies.

Nematic and ferroelectric liquid crystals have also been used as the active layer in several SLMs. Since the electrooptic effect in liquid crystals is based on the mechanical reorientation of molecular dipoles, it is to be expected that liquid crystals are faster than the DMD-type devices. Modulators using ferroelectric liquid crystals have exhibited moderate switching speeds (150 μsec to 100 nsec), low-power consumption, VLSI compatible switching voltages (5-10 V), high extinction ratios, high resolution and large apertures. However, these devices suffer from the drawbacks of limited liquid crystal lifetimes and operating temperature ranges. In addition, the manufacturing process is complicated by alignment problems and film thickness uniformity issues.

Magnetooptic modulation schemes have been used to achieve faster switching speeds and to provide an optical pattern memory cell. Although these devices, in addition to achieving fast switching speeds, can achieve large contrast ratios, they suffer from a low (<10%) throughput

1　efficiency and are, therefore, often unsuitable for many
2　applications.
3　　　　The need is therefore for a light modulation device
4　which overcomes these drawbacks.
5　　　　Beside SLMs, another area of use of light modulators
6　is in fiber optics. Fiber optic modulators are
7　electronically controlled devices that modulate light
8　intensity and are designed to be compatible with optical
9　fibers. For high speed communication applications,
10　lithium niobate ($LiNbO_3$) traveling wave modulators
11　represent the state-of-the-art, but there is a need for
12　low power, high efficiency, low loss, inexpensive fiber
13　optic modulators, that can be integrated with silicon
14　sensors and electronics, for data acquisition and medical
15　applications. A typical use of a modulator combined
16　with fiber optic technology, for example, is a data
17　acquisition system on an airplane which consists of a
18　central data processing unit that gathers data from remote
19　sensors. Because of their lightweight and electro-
20　magnetic immunity characteristics, fiber optics provide an
21　ideal communication medium between the processor and the
22　sensors which produce an electrical output that must be
23　converted to an optical signal for transmission. The most
24　efficient way to do this is to have a continuous wave
25　laser at the processor and a modulator operating in
26　reflection at the sensor. In this configuration, it is
27　also possible to deliver power to the sensor over the
28　fiber.
29　　　　In this type of application the modulator should
30　operate with high contrast and low insertion loss to
31　maximize the signal to noise ratio and have low power
32　consumption. It should further be compatible with silicon
33　technology because the sensors and signal conditioning
34　electronics used in these systems are largely implemented
35　in silicon.
36　　　　Another use of a modulator combined with fiber optic
37　technology is in the monitoring of sensors that are
38　surgically implanted in the human body. Here optical
39　fibers are preferred to electrical cables because of their

1   galvanic isolation, and any modulator used in these
2   applications should exhibit high contrast combined with
3   low insertion loss because of signal to noise
4   considerations. Furthermore, as size is important in
5   implanted devices, the modulator must be integratable with
6   silicon sensors and electronics.

7   There exist no prior art devices that have the
8   characteristics enumerated above. Modulators based on the
9   electro-optic, Franz-Keldysh, Quantum-Confined-Stark or
10   Wannier-Stark effect in III-V semiconductors have high
11   contrast and low insertion loss, but are expensive and not
12   compatible with silicon devices. Waveguide modulators
13   employing glass or epi-layers on silicon, require too much
14   area and too complex fabrication to be easily integratable
15   with other silicon devices. Silicon modulators that do
16   not employ waveguides and that are based on the plasma
17   effect, require high electrical drive power and do not
18   achieve high contrast.

19   The need is therefore for a light modulator which can
20   be used with fiber optic technology with low power, high
21   efficiency, low loss, low cost and compatibility with
22   multimode optical fibers and silicon technology.

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SUMMARY OF THE INVENTION

Objects of the Invention

Accordingly, it is an object of this invention to provide a light modulator which alone or together with other modulators exhibits most of the following characteristics: high resolution, high speed (Khz frame rates), gray levels (100 levels), high contrast ratio or modulation depth, optical flatness, VLSI compatible, easy handling capability and low cost.

A further object of this invention is to provide a light modulator which has a tolerance for high optical power and good optical throughput.

Yet another object of this invention is to provide a light modulator which is compatible with CMOS technology.

Still another object of this invention is to provide a light modulator capable of use with fiber optic technology.

A final object of this invention is to provide a light modulator which is capable of modulating white light to produce colored light.

Summary

Briefly a presently preferred embodiment of this invention includes a modulator for modulating incident rays of light, the modulator comprising a plurality of equally spaced apart beam elements, each of which includes a light reflective planar surface. The elements are arranged parallel to each other with their light reflective surfaces parallel to each other. The modulator includes means for supporting the beam elements in relation to one another and means for mcving the beam elements relative to one another so that the beams move between a first configuration wherein the modulator acts to reflect the incident rays of light as a plane mirror, and a second configuration wherein the modulator diffracts the incident rays of light as they are reflected therefrom. In operation, the light reflective surfaces of

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1 the beam elements remain parallel to each other in both
2 the first and the second configurations and the
3 perpendicular spacing between the reflective surfaces of
4 adjacent beam elements is equal to m/4 times the
5 wavelength of the incident rays of light, wherein m = an
6 even whole number or zero when the beam elements are in
7 the first configuration and m = an odd number when the
8 beam elements are in the second configuration.

9 One embodiment of this invention includes a
10 reflective deformable grating light modulator, with a
11 grating amplitude that can be controlled electronically,
12 consisting of a reflective substrate with a deformable
13 grating suspended above it. In its undeformed state, with
14 no voltage applied between the elements of the grating and
15 the substrate, the grating amplitude is one half of the
16 wavelength of the incoming light. Since the round-trip
17 path difference between the light reflected from the top
18 and bottom of the grating is one wavelength, no
19 diffraction occurs. When a voltage is applied between the
20 grating elements and the substrate, the electrostatic
21 force pulls the elements down to cause the grating
22 amplitude to become one quarter of the wavelength so that
23 reflections from the elements and the substrate add
24 destructively, causing the light to be diffracted. If the
25 detection system for the reflected light has a numerical
26 aperture which accepts only the zero order beam, a
27 mechanical motion of only one quarter of a wavelength is
28 sufficient to modulate the reflected light with high
29 contrast.

30 Typically the grating is formed by lithographically
31 etching a film made of silicon nitride, aluminum, silicon
32 dioxide or any other material which can be
33 lithographically etched.

34 The deformable grating modulator of this invention
35 has the advantage that it is implemented in silicon
36 technology, using micromachining and sacrificial etching
37 of thin films to fabricate the gratings. Circuitry for
38 addressing and multiplexing can be manufactured on the
39 same silicon substrate and thus be directly integrated

with the modulator. Direct integration with electronics is an important advantage over non-silicon based technologies like liquid crystal and electrooptic SLMs. Moreover, the device demonstrates simplicity of fabrication and can be manufactured with only a few lithographic steps.

A further advantage of the deformable grating modulator is that because the deformable grating modulator utilizes diffraction rather than deflection of a light beam, the required mechanical motions are reduced from several microns (as in deformable mirror devices) to tenths of a micron, thus allowing for a potential three orders of magnitude in increase in speed. This speed is comparable to the fastest liquid crystal modulators, but without the device suffering the same complexity in the manufacturing process.

Still a further advantage of these devices is that the required motion of the grating elements is only one quarter of a wavelength, which means that elements with high resonance frequencies can be used.

These and other objects and advantages of the present invention will no doubt become apparent to those skilled in the art after having read the following detailed description of the preferred embodiment which is illustrated in the several figures of the drawing.

IN THE DRAWING

This invention will now be further illustrated with reference to the accompanying drawing in which:

FIG. 1(a)-(d) are cross-sections through a silicon substrate illustrating the manufacturing process of a reflective, deformable diffraction grating according to one embodiment of the invention;

FIG. 2 is an isometric, partially cut-away view of the diffraction grating, the manufacture of which is illustrated in FIG. 1.

FIG. 3 illustrates the operation of the grating of FIG. 2 in its "non-defracting" mode;

1   FIG. 4 and illustrates the operation of the grating
2 of FIG. 3 in its "diffracting" mode;
3   FIG. 5 is a cross-section similar to that in FIG. 3,
4 illustrating an alternative embodiment of the grating in
5 its "non-defracting" mode;
6   FIG. 6 is a cross-section similar to that in FIG. 4,
7 illustrating the grating in FIG. 8 in its "defracting"
8 mode;
9   FIG. 7 is a pictoral view illustrating a further
10 embodiment of the grating;
11   FIG. 8 is a cross-section along line 8-8 in FIG. 7;
12   FIG. 9 is a graphical representation of the
13 modulation of a laser beam by the grating of the
14 invention;
15   FIG. 10 is an illustration of how the diffraction
16 grating of the invention can be combined with other
17 gratings to form a complex modulator; and
18   FIG. 11 illustrates the operation of the grating in
19 the modulation of colored light.
20
21   DESCRIPTION OF PREFERRED EMBODIMENTS
22   The fabrication steps required to produce a
23 reflective deformable grating 10 according to this
24 invention are illustrated in FIG. 1(a)-(d).
25   The first step, as illustrated in FIG. 1(a), is the
26 deposition of an insulating layer 11 made of stoichemetric
27 silicon nitride topped with a buffer layer of silicon
28 dioxide followed by the deposition of a sacrificial
29 silicon dioxide film 12 and a low-stress silicon nitride
30 film 14, both 213 nm thick, on a silicon substrate 16.
31 The low-stress silicon nitride film 14 is achieved by
32 incorporating extra silicon (beyond the stoichiometric
33 balance) into the film, during the deposition process.
34 This reduces the tensile stress in the silicon nitride
35 film to roughly 200 MPa.
36   In the second step, which is illustrated in FIG.
37 1(b), the silicon nitride film 14 is lithographically
38 patterned into a grid of grating elements in the form of
39 elongate beams 18.   In an individual grating, all the

beams are of the same dimension and are arranged parallel
to one another with the spacing between adjacent beams
equal to the beam width. Depending on the design of the
grating, however, beams could typically be 1, 1.5 or $2\mu m$
wide with a length that ranges from $10\mu m$ to $120\mu m$. After
this lithographic patterning process a peripheral silicon
nitride frame 20 remains around the entire perimeter of
the upper surface of the silicon substrate 16. This frame
20 is further illustrated in FIG. 2 and will be more fully
described below with reference to that figure.

After the patterning process of the second step, the
sacrificial silicon dioxide film 12 is etched in
hydrofluoric acid, resulting in the configuration
illustrated in FIG. 1(c). It can be seen that each beam
18 now forms a free standing silicon nitride bridge, 213
nm thick, which is suspended a distance of 213nm (this
being the thickness of the etched away sacrificial film
12) clear of the silicon substrate. As can further be
seen from this figure the silicon dioxide film 12 is not
entirely etched away below the frame 20 and so the frame
20 is supported, a distance of 213 nm, above the silicon
substrate 16 by this remaining portion of the silicon
dioxide film 12. The beams 18 are stretched within the
frame and kept straight by the tensile stress imparted to
the silicon nitride film 14 during the deposition of that
film.

The last fabrication step, illustrated in FIG. 1(d),
is sputtering, through a stencil mask, of a 50 nm thick
aluminum film 22 to enhance the reflectance of both the
beams 18 and the substrate 16 and to provide a first
electrode for applying a voltage between the beams and the
substrate. A second electrode is formed by sputtering an
aluminum film 24, of similar thickness, onto the base of
the silicon substrate 16.

The final configuration of the grating is illustrated
in FIG. 2. Here it can be seen that the beams 18 together
with the frame 20 define a grating which, as will be later
explained, can be used for modulating a light beam.
Furthermore, and as can be gathered from the above

1   described manufacturing process, the frame is formed
2   integrally with the beams 18 and thus provides a
3   relatively rigid supporting structure which maintains the
4   tensile stress within the beams 18. In so doing, and as
5   the frame 20 is supported by the remainder of the silicon
6   dioxide film 12 that was not etched away, the beams are
7   kept straight and a distance of 213 nm above the surface
8   of the silicon substrate 16.

9   The operation of the deformable grating 10, formed by
10   the above process, is illustrated with reference to FIG.
11   3 and 4. Before commencing the description of how the
12   grating operates, however, it should be recalled that, in
13   this case, each of the beams 18 are 213 nm thick and are
14   suspended a distance of 213 nm clear of the substrate 16.
15   This means that the distance from the top of each beam to
16   the top of the substrate is 426 nm. Similarly, the
17   distance between the top of the reflective surface on the
18   beams to the top of the reflective surface on the
19   substrate is also 426 nm. This distance is known as the
20   grating amplitude.

21   In FIG. 3 the grating 10 is shown with no voltage
22   applied between the substrate 16 and the individual beams
23   18 and with a lightwave, generally indicated as 26, of a
24   wavelength λ = 852 nm is incident upon the it. The
25   grating amplitude of 426 nm is therefore equal to half of
26   the wavelength of the incident light and, therefore, the
27   total path length difference for the light reflected from
28   the beams and from the substrate equals the wavelength of
29   the incident light. As a result, light reflected from the
30   beams and from the substrate add in phase and the grating
31   10 acts to reflect the light as a flat mirror.

32   However, as illustrated in FIG. 4, when a voltage is
33   applied between the beams 18 and the substrate 16 the
34   electrostatic forces pull the beams 18 down onto the
35   substrate 16, with the result that the distance between
36   the top of the beams and the top of the substrate is now
37   213 nm. As this is one quarter of the wavelength of the
38   incident lights, The total path length difference for the
39   light reflected from the beams and from the substrate is

1   now one half of the wavelength (426 nm) of the incident

2   light and the reflections interfere destructively, causing

3   the light to be diffracted, indicated as 28.

4   Thus, if this grating is used in combination with a

5   system, for detecting the reflected light, which has a

6   numerical aperture sized to detect one order of diffracted

7   light from the grating e.g., the zero order, this grating

8   can be used to modulate the reflected light with high

9   contrast.

10   In FIGS. 5 and 6 an alternative embodiment of the

11 diffraction grating 30 of the invention is illustrated.

12 In this embodiment the grating 30 consists of a plurality

13 of equally spaced, equally sized, fixed beams 32 and a

14 plurality of equally spaced, equally sized, movable beams

15 34 in which the movable beams 34 lie in the spaces between

16 the fixed beams 32. Each fixed beam 32 is supported on

17 and held in position by a body of supporting material 36

18 which runs the entire length of the fixed beam 32. The

19 bodies of material 36 are formed during a lithographic

20 etching process in which the material between the bodies

21 36 is removed.

22   As can be seen from FIG. 5 the fixed beams 32 are

23 arranged to be coplanar with the movable beams 34 and

24 present a flat upper surface which is coated with a

25 reflective layer 38. As such the grating 30 acts as a

26 flat mirror when it reflects incident light, however, when

27 a voltage is applied between the beams and an electrode 40

28 at the base of the grating 30 the movable beams 34 move

29 downwards as is illustrated in FIG. 6. By applying

30 different voltages the resultant forces on the beams 34

31 and, therefore, the amount of deflection of the movable

32 beams 34 can be varied. Accordingly, when the grating

33 amplitude (defined as the perpendicular distance $\underline{d}$ between

34 the reflective layers 38 on adjacent beams) is m/4 times

35 the wavelength of the light incident on the grating 30,

36 the grating 30 will act as a plane mirror when m = 0, 2,

37 4... (i.e. an even number or zero) and as a reflecting

38 diffraction grating when m = 1, 3, 5... (i.e. an odd

39 number). In this manner the grating 30 can operate to

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1 modulate incident light in the same manner as the grating
2 10 illustrated in FIGS. 1 to 4.
3   Yet another embodiment of the diffraction grating of
4 the invention is illustrated in FIGS. 7 and 8. As with
5 the grating 10 in FIGS. 1 to 4 this grating 41 consists of
6 a sacrificial silicon dioxide film 42, a silicon nitride
7 film 44 and a substrate 46. In this embodiment, however,
8 the substrate 46 has no reflective layer formed thereon
9 and only the silicon nitride film 44 has a reflective
10 coating 45 formed thereon. As is illustrated in FIG. 7
11 the deformable beams 48 are coplanar in their undeformed
12 state and lie close to one another so that together they
13 provide a substantially flat reflective surface. The
14 beams 48 are, however, formed with a neck 50 at either
15 end, which is off-center of the longitudinal center line
16 of each of the beams 48.
17   When a uniformly distributed force, as a result of an
18 applied voltage for example, is applied to the beams 48
19 the resultant force $\underline{F}$, for each beam 48, will act at the
20 geometric center 52 of that beam. As each resultant force
21 $\underline{F}$ is off-set from the axis of rotation 54 (which coincides
22 with the centerline of each neck 50), a moment of rotation
23 or torque is applied to each beam 48 which results in a
24 rotation of each beam 48 about its axis 54 to the position
25 48' indicated in broken lines. This is known as "blazing"
26 a diffraction grating.
27   As can be seen from FIG. 8, the reflective planes 56
28 of the beams 48 remain parallel to each other even in this
29 "blazed" configuration and therefore, the grating
30 amplitude $\underline{d}$ is the perpendicular distance between the
31 reflective surfaces of adjacent beams. This "blazed"
32 grating will operate to diffract light in the same manner
33 as a sawtooth grating.
34   Although not illustrated in any of FIGS. 1 to 8, it
35 will be apparent that a deformable diffraction grating can
36 be constructed in which, in its undeformed state, all the
37 reflective elements are in the form of movable beam
38 elements arranged parallel, adjacent and coplanar with
39 each other. In this type of grating not only the grating

1 amplitude (i.e., the perpendicular distance between
2 adjacent reflective surfaces) can be varied but also the
3 average height of all the reflective surfaces can be
4 changed by moving all the beams relative to a fixed datum.
5 This arrangement has the advantage that both the amplitude
6 and the phase of the reflected/diffracted light can be
7 modulated.
8 The electrical, optical and mechanical
9 characteristics of a number of modulators, similar in
10 design to the modulator illustrated with reference to
11 FIGS. 1 to 4 but of different dimensions were investigated
12 by using a Helium Neon laser (of 633 nm wavelength)
13 focused to a spot size of 36μm on the center portion of
14 each modulator. This spot size is small enough so that
15 the curvature of the beams in the region where the
16 modulator was illuminated can be neglected, but is large
17 enough to allow the optical wave to be regarded as a plane
18 wave and covering enough grating periods to give good
19 separation between the zero and first order diffraction
20 modes resulting from the operation of the grating. It was
21 discovered that grating periods of (i.e.) the distance
22 between the centerlines of two adjacent beams in the
23 grating, 2,3 and 4 μm and a wavelength of 633 nm resulted
24 in first order diffraction angles of 18˚, 14˚ and 9˚
25 respectively.
26 One of these first order diffracted light beams was
27 produced by using a 120 μm-long grating modulator with 1.5
28 μm-wide beams at atmospheric pressure together with a HeNe
29 light beam modulated at a bit rate of 500 kHz. detected by
30 a low-noise photoreceiver and viewed on an oscilloscope.
31 The resulting display screen 30 of the oscilloscope is
32 illustrated in FIG. 9.
33 However, before proceeding with a discussion of the
34 features illustrated in this figure, the resonant
35 frequency of the grating elements should first be
36 considered.
37 The resonant frequency of the mechanical structure of
38 the grating of the invention was measured by driving the
39 deformable grating modulator with a step function and

observing the ringing frequency. The area of the aluminum on the deformable grating modulator is roughly 0.2 cm^2, which corresponds to an RC limited 3-dB bandwidth of 1 MHz with roughly 100 ohms of series resistance. This large RC time constant slowed down the step function, however, enough power existed at the resonant frequency to excite vibrations, even in the shorter beams. Although the ringing could be observed in normal atmosphere, the Q-factor was too low (approximately 1.5) for accurate measurements, so the measurements were made at a pressure of 150 mbar. At this pressure, the Q-factor rose to 8.6, demonstrating that air resistance is the major damping mechanism, for a grating of this nature, in a normal atmosphere.

Nonetheless, it was found that due to the high tensile stress in the beams, tension is the dominant restoring force, and the beams could therefore be modeled as vibrating strings. When this was done and the measured and theoretically predicted resonance frequencies compared, it was found that the theory is in good agreement with the experimental values, particularly when considering the uncertainty in tensile stress and density of the beams. As it is known that the bandwidth of forced vibrations of a mechanical structure is simply related to the resonance frequency and Q-factor, a Q-factor of 1.5 yields a 1.5 dB bandwidth of the deformable grating modulator 1.4 times larger than the resonance frequency. The range of bandwidths for these gratings is therefore from 1.8 MHz for the deformable grating modulator with 120 μm beams to 6.1 MHz for the deformable grating modulator with 40 μm beams.

Returning now to FIG. 9, it should be noted that with an applied voltage swing of 3 V, a contrast of 16dB for the 120 μm-long bridges could be observed. Here the term "modulation depth" is taken to mean the ratio of the change in optical intensity to peak intensity.

The input (lower trace 62) on the screen 60 represents a pseudo-random bit stream switching between 0 and -2.7 V across a set of grating devices on a 1 cm by 1

1   cm die.   The observed switching transient with an initial
2   fast part followed by a RC dominated part, is caused by
3   the series resistance of the deformable grating modulator,
4   which is comparable to a 50 ohm source resistance.
5   The output (upper trace 64) on the screen corresponds
6   to the optical output of a low-noise photoreceiver
7   detecting the first diffraction order of the grating used.
8   The output (upper trace 64) from the deformable grating is
9   high when the beams are relaxed and low when the beams are
10   deflected.   Ringing is observed only after the rising
11   transient, because of the quadratic dependence of the
12   electro-static force on the voltage (during switching from
13   a voltage of -2.7 V to 0 V, the initial, faster part of
14   the charging of the capacitor corresponds to a larger
15   change in electro-static force, than when switching the
16   opposite way).   This ringing in the received signal
17   indicates a decay close to critical damping.
18   Furthermore, it was found that because the
19   capacitance increases as the beams are pulled toward the
20   substrate, the voltage needed for a certain deflection is
21   not a monotonically increasing function of this
22   deflection.   At a certain applied voltage condition, an
23   incremental increase in the applied voltage causes the
24   beams to be pulled spontaneously to the substrate (to
25   latch) and this voltage is known as the "switching
26   voltage" of the modulator.   The switching voltage was
27   found to be 3.2 V for gratings with 120 μm long beams and,
28   if it is assumed that tension dominates the restoring
29   forces, the switching voltage is inversely proportional to
30   the beam length and therefore, the predicted switching
31   voltage for 40 μm long beams will be 9.6 V.
32   The importance of the switching voltage is that below
33   this voltage, the deformable grating modulator can be
34   operated in an analog fashion, however, if a voltage
35   greater than the switching voltage is applied to the
36   modulator it acts in a digital manner. Nonetheless, it is
37   important to note that operating the modulator to the
38   point of contact is desirable from an applications point
39   of view, because as discussed above when the beams are

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1   deflected electrostatically, an instability exists once
2   the beam deflection goes beyond the halfway point. This
3   results in hysteretic behavior which will "latch" the beam
4   in the down position. This latching feature gives the
5   modulator the advantages of an active matrix design
6   without the need for active components. A further
7   advantage of this latching feature is that once the beam
8   has "latched" it requires only a very small "holding
9   voltage", much smaller than the original applied voltage,
10 to keep the beam in its latched configuration. This
11 feature is particularly valuable in low power applications
12 where efficient use of available power is very important.
13   Finally, it was discovered that when the beams of the
14 modulators are brought into contact with the substrate
15 they could stick. This can be solved by adding small
16 ridges below the beams to reduce the contact area between
17 the beams and the substrate and thereby reduce the
18 sticking problem.
19   The use of the modulator of this invention in
20 displays requires high yield integration of individual
21 modulator elements into 2-D arrays such as that
22 illustrated in FIG. 10 which shows a plurality of grating
23 modulators which can be used to provide a gray-scale
24 operation. Each of the individual modulators 66, 68, 70,
25 72 consist of a number of beams and gray-scale can be
26 obtained by addressing each modulator in a binary-weighted
27 manner. The hysteresis characteristic for latching (as
28 described above) can be used to provide gray-scale
29 variation without analog control of the voltage supplied
30 to individual grating modulator elements.
31   In FIG. 11 the use of the grating, in combination
32 with other gratings, for modulating white light to produce
33 colored light is illustrated. This approach takes
34 advantage of the ability of a grating to separate a light
35 spectrum into its consistent colors. By constructing
36 separate red, green and blue modulation elements each with
37 a grating designed to diffract the appropriate color into
38 an optical system, a color display which is white light

1   illuminated can be achieved. This approach is attractive

2   for large area projection displays.

3   In summary, the reflective, deformable grating light

4   modulator of this invention is a device which exhibits

5   high resolution (40 by 40 μm^2 to 100 μm^2); high response

6   times/large bandwidth (2 to 6 MHz); high contrast ratio

7   (close to 100% modulation with a 3V switching voltage); is

8   polarization independent and easy to use. This device

9   also has tolerance for high optical power, has good

10   optical throughput, is simple to manufacture, CMOS

11   compatible, and has application in a wide range of fields

12   including use as an SLM and with fiber optic technology.

13   Although the present invention has been described

14   above in terms of specific embodiments, it is anticipated

15   that alterations and modifications thereof will no doubt

16   become apparent to those skilled in the art. It is

17   therefore intended that the following claims be

18   interpreted as covering all such alterations and

19   modifications as fall within the true spirit and scope of

20   the invention.

21   What is claimed is:

-18-

CLAIMS

1.   A modulator for modulating incident rays of light, the modulator comprising:
    a plurality of equally spaced apart beam elements, each including a light reflective planar surface, the elements being arranged parallel to each other and with the light reflective surfaces of the beam elements being parallel to each other;
    means for supporting the beam elements in relation to one another; and
    means for moving the beam elements relative to one another between a first configuration wherein the modulator acts to reflect the incident rays of light as a plane mirror, and a second configuration wherein the modulator diffracts the incident rays of light as they are reflected therefrom.

2.   A modulator as recited in claim 1, wherein the light reflective surfaces of the beam elements are parallel to each other in both the first and the second configurations.

3.   A modulator as recited in claim 2, wherein the perpendicular spacing between the reflective surfaces of adjacent beam elements is equal to $m/4$ times the wavelength of the incident rays of light, wherein m = an even whole number or zero when the beam elements are in the first configuration and m = an odd number when the beam elements are in the second configuration.

4.   A modulator as recited in claim 3, wherein the means for moving the beam elements operates to rotate the beam elements when moving them relative to one another.

5.   A modulator as recited in claim 3, wherein alternate beam elements are fixed relative to the support means.

SUBSTITUTE SHEET

1   6.   A modulator as recited in claim 1, wherein the means
2   for applying force to the beams comprises means for
3   applying an electrostatic force to the beam elements.

1   7.   A modulator as recited in claim 6, wherein the
2   reflective surfaces are formed by metallic layers.

1   8.   A modulator as recited in claim 7, wherein the means
2   for applying electrostatic force includes the metallic
3   layers.

1   9.   A modulator as recited in claim 3, wherein the planar
2   reflective surfaces of the beam elements are equal in
3   dimensions and are substantially rectangular in plan.

1   10. A modulator as recited in claim 4, wherein the beam
2   elements are resilient.

1   11. A modulator for modulating a beam of incident light,
2   the modulator comprising;
3   a planar light reflective surface;
4   a deformable grating having a planar light reflective
5   surface, the deformable grating being arranged with its
6   reflective surface being parallel to and spaced from the
7   planar reflective surfaces; and
8   means for moving the grating towards the planar
9   reflective surface while at the same time maintaining the
10   reflective surface of the grating substantially parallel
11   to the planar reflective surface;
12   whereby, when the perpendicular spacing between the
13   respective light reflective surfaces is equal to m/4 times
14   the wavelength of the incident light and m = an even whole
15   number or zero the modulator acts to reflect the incident
16   light as a plane mirror and when m = an odd whole number
17   the modulator diffracts the incident light as it reflects
18   it, thereby providing the modulation of the beam of light.

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1   12. A modulator as recited in claim 11, wherein the
2   grating comprises a plurality of equally sized and equally
3   spaced apart parallel rectangular beam elements.

1   13. A modulator as recited in claim 12, wherein the
2   spacing between each of the beam elements is substantially
3   equal to the transverse width of each of the beam
4   elements.

1   14. A modulator as recited in claim 13, wherein the
2   spacing between the planar reflective surface and the
3   reflective surface of the deformable grating is equal to
4   half the wavelength of the beam of incident light.

1   15. A modulator as recited in claim 14, wherein the means
2   for moving the grating towards the planar reflective
3   surface comprises means for applying an electrostatic
4   force between the planar reflective surface and the
5   reflective surface of the grating.

1   16. A modulator as recited in claim 15, wherein the
2   thickness of each beam element is equal to half the
3   spacing between the two reflective surfaces.

1   17. A modulator as recited in claim 12 wherein the
2   grating comprises a deformable resilient material.

1   18. A method of modulating a ray of light, comprising the
2   steps of:
3   causing the ray to impinge on a plurality of equally
4   spaced apart beam elements, each including a light
5   reflective planar surface, the elements being arranged
6   parallel to each other and with the light reflective
7   surfaces of the beam elements being parallel to each
8   other; and
9   moving the beam elements relative to one another
10   between a first configuration wherein the modulator acts
11   to reflect the incident rays of light as a plane mirror,
12   and a second configuration wherein the modulator diffracts

13   the incident rays of light as they are reflected
14   therefrom.

1   19.   A method of modulating a ray of light as recited in
2   claim 18, wherein the beam elements are moved to cause the
3   perpendicular spacing between the reflective surfaces of
4   adjacent beam elements to be equal to m/4 times the
5   wavelength of the incident rays of light, wherein m = an
6   even whole number or zero when the beam elements are in
7   the first configuration and m = an odd number when the
8   beam elements are in the second configuration.

1   20. A method as recited in claim 19, wherein the
2   thickness of each beam element is equal to half the
3   spacing between the two reflective surfaces.

1   21.   A method of modulating a ray of light as recited in
2   claim 20, wherein the beam elements are caused to move
3   relative to one another by applying an electrostatic force
4   to the elements.

1   22. A modulator for modulating incident rays of light,
2   the modulator comprising a plurality of elements arranged
3   to act in concert to modulate the rays by means of
4   diffraction, each element including:
5   a plurality of equally spaced apart beam elements,
6   each including a light reflective planar surface, the
7   elements being arranged parallel to each other and with
8   the light reflective surfaces of the beam elements being
9   parallel to each other;
10   means for supporting the beam elements in relation to
11   one another; and
12   means for moving the beam elements relative to one
13   another between a first configuration wherein the
14   modulator acts to reflect the incident rays of light as a
15   plane mirror, and a second configuration wherein the
16   modulator diffracts the incident rays of light as they are
17   reflected therefrom.

1   23. A modulator as recited in claim 22, wherein the light
2   reflective surfaces of the beam elements are parallel to
3   each   other   in   both   the   first   and   the   second
4   configurations.

1   24. A modulator as recited in claim 23, wherein the
2   perpendicular spacing between the reflective surfaces of
3   adjacent beam elements is equal to m/4 times the
4   wavelength of the incident rays of light, wherein m = an
5   even whole number or zero when the beam elements are in
6   the first configuration and m = an odd number when the
7   beam elements are in the second configuration.

1   25. A modulator as recited in claim 24, wherein the means
2   for moving the beam elements operates to rotate the beam
3   elements when moving them relative to one another.

1   26. A modulator as recited in claim 25, wherein alternate
2   beam elements are fixed relative to the support means.

1   27. A modulator as recited in claim 4, wherein the means
2   for moving the beam elements comprises means for applying
3   an electrostatic force between the planar reflective
4   surface and the reflective surface of the grating.

1   28. A modulator as recited in claim 27 wherein the beam
2   elements comprise a deformable resilient material.

1/4
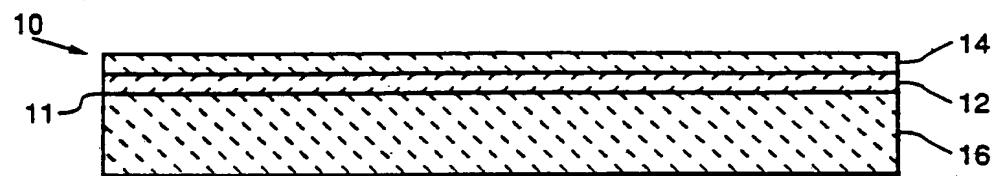
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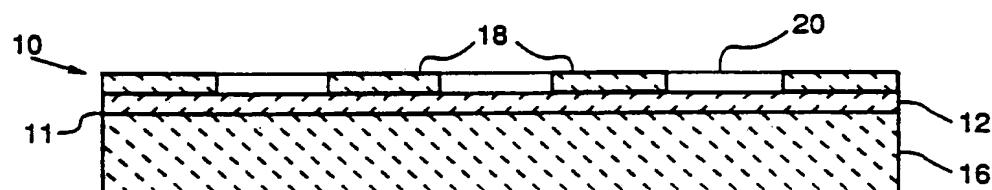
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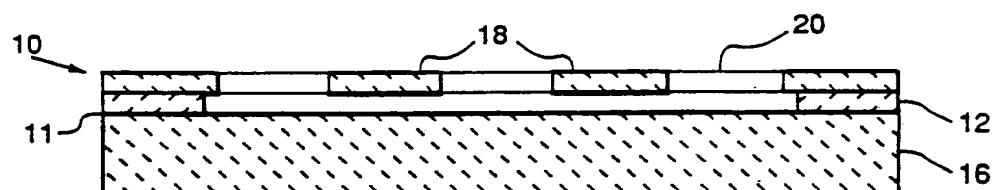
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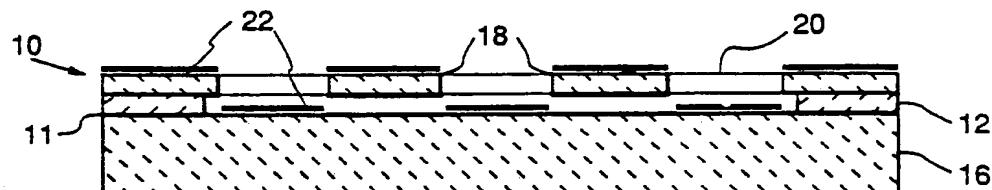
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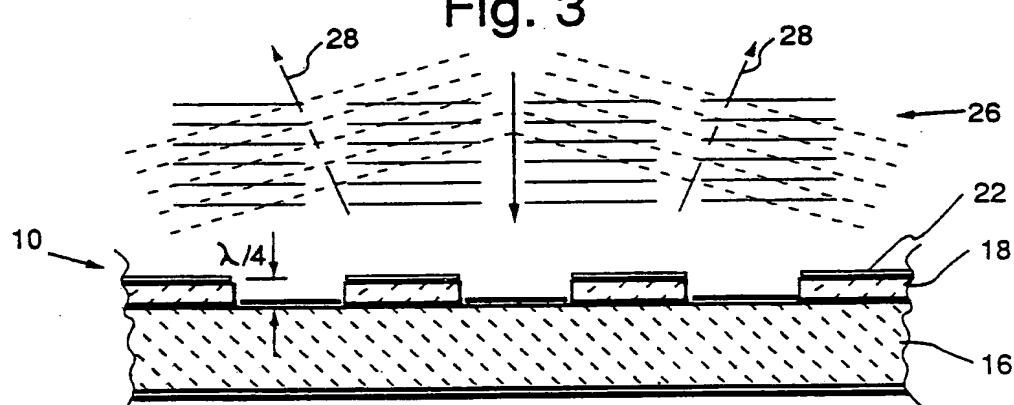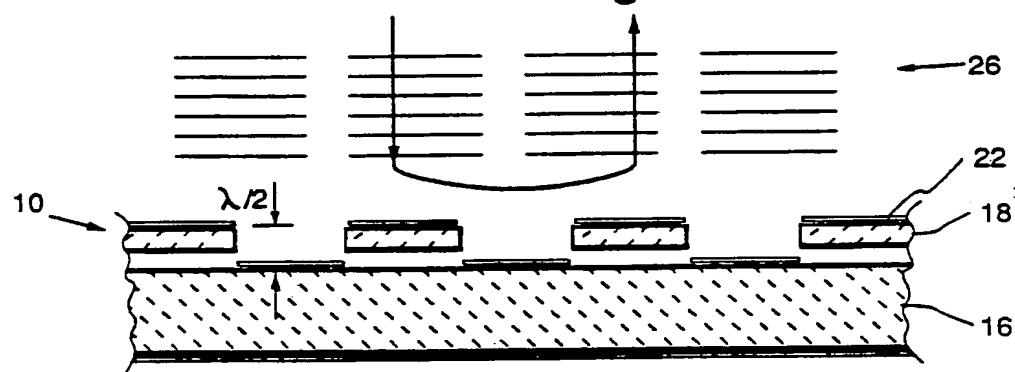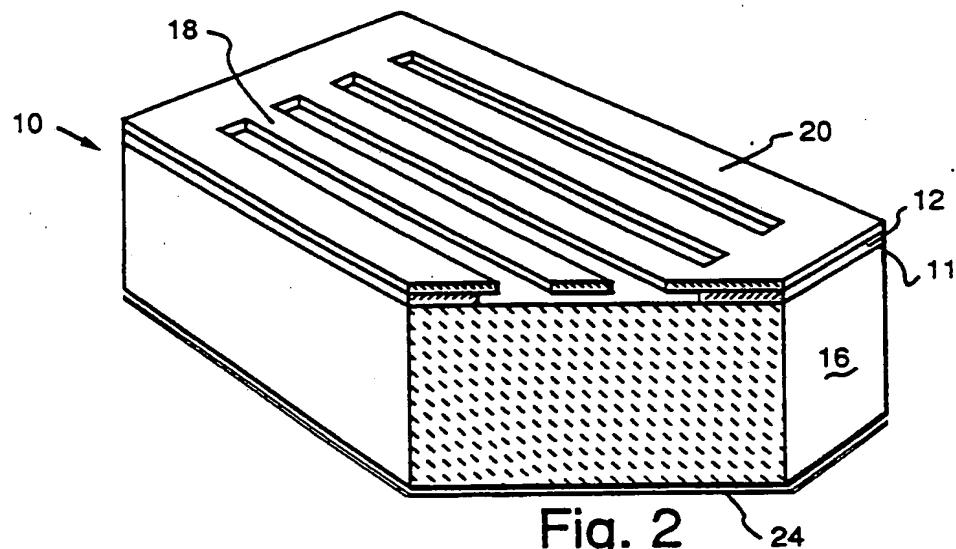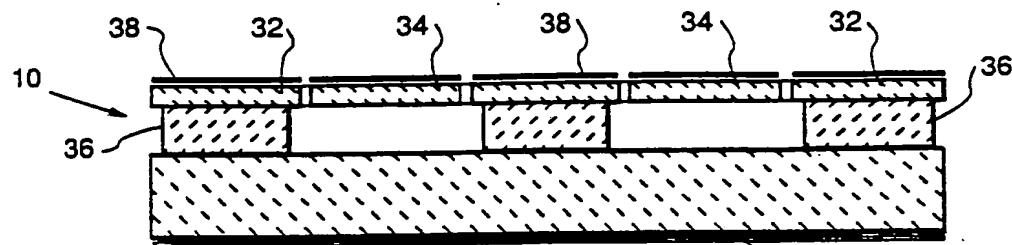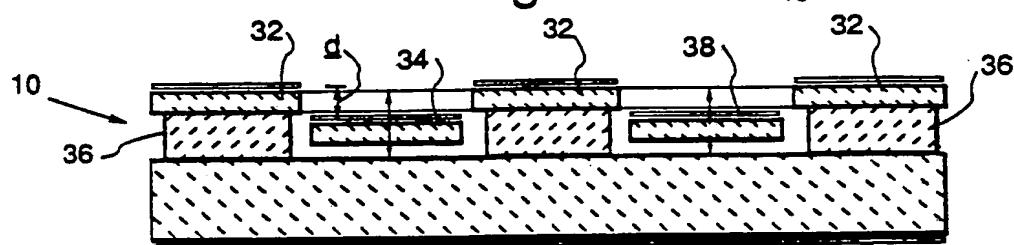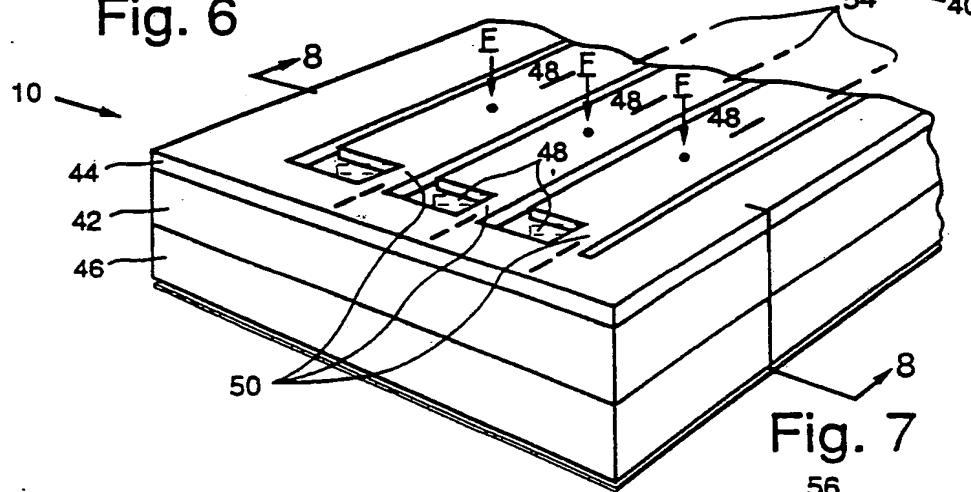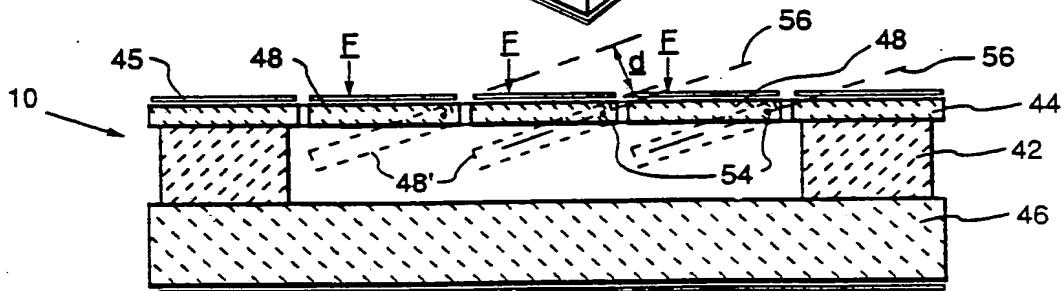
Fig. 2

Fig. 3

Fig. 4

Fig. 5

Fig. 6

Fig. 7

Fig. 8
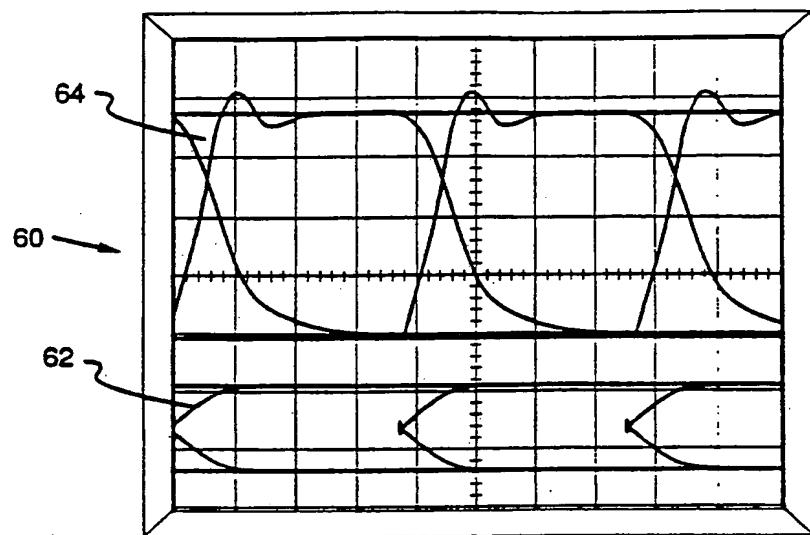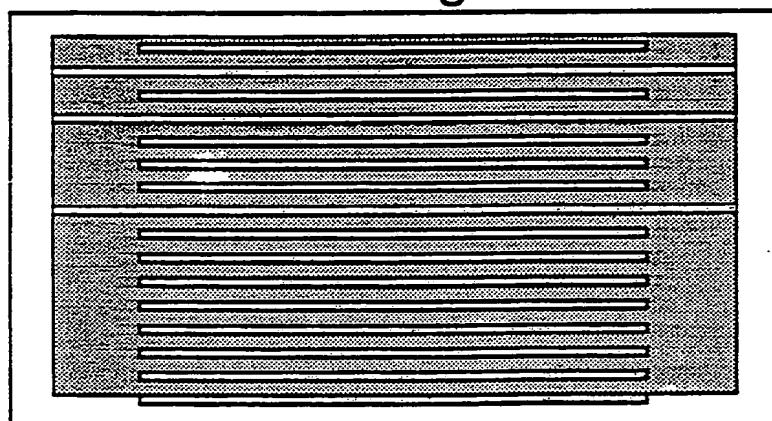
## Fig. 9

Fig. 10
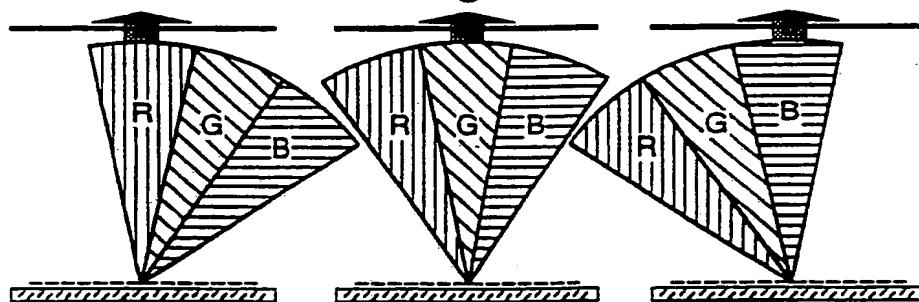
Fig. 11

INTERNATIONAL SEARCH REPORT

A.	CLASSIFICATION OF SUBJECT MATTER

IPC(5) :G02B 5/18, 26/00
US CL :359/566,572,573,291
According to International Patent Classification (IPC) or to both national classification and IPC

B.	FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

U.S. : 359/566,572,573,291 359/231,295,298,299,302,558,569

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

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Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

Please See Extra Sheet.

C.	DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	US,A, 4,596,992 (Hornbeck) 24 June 1986 See col. 7, lines 40+ and col. 8, lines 33+ see Fig. 12C.	1,2,6-8,22 23
X	US,A, 4,492,435 (Banton et al.) 08 January 1985 See Fig. 5.	11,12

☐ Further documents are listed in the continuation of Box C. ☐ See patent family annex.

	Special categories of cited documents:	"T"	later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
"A"	document defining the general state of the art which is not considered to be part of particular relevance		
"E"	earlier document published on or after the international filing date	"X"	document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
"L"	document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)	"Y"	document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art
"O"	document referring to an oral disclosure, use, exhibition or other means		
"P"	document published prior to the international filing date but later than the priority date claimed	"&"	document member of the same patent family

Date of the actual completion of the international search	Date of mailing of the international search report
16 JUNE 1993	04 AUG 1993
Name and mailing address of the ISA/US Commissioner of Patents and Trademarks Box PCT Washington, D.C. 20231	Authorized officer JOHN JUBA
Facsimile No. NOT APPLICABLE	Telephone No. (703) 308-4812

Form PCT/ISA/210 (second sheet)(July 1992)*

B. FIELDS SEARCHED

Electronic data bases consulted (Name of data base and where practicable terms used):

APS   Diffract()
    Reflect()
    Grating   Phase Grating
    Electrostatic   Deform()
    Quarter Wave